
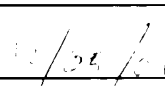



Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. M1221657		SERIAL NO. Unknown	
LIST OF ART CITED BY APPLICANT <small>Use several sheets if necessary.</small>				APPLICANT Cem. Basceri et al.			
				FILING DATE Filed Herein		GROUP Unknown	
U.S. PATENT DOCUMENTS							
*Examiner Initials	Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate	
EE	AA		Cem. Basceri et al. as filed			Filed Concurrently	
EE	AB	09/26/516	Cem. Basceri as filed and as amended.			01/03/00	
EE	AC	09/580/733	Cem. Basceri as filed.			05/26/00	
EE	AD	5/459/635	10/17/95 Tomozawa et al.	361	321.5		
EE	AE	5/618/761	04/08/97 Eguchi et al.	438	785		
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FOREIGN PATENT DOCUMENTS							
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)							
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EXAMINER			DATE CONSIDERED				
			12/04/01				
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P.O. # 1420 AUG 29 2001		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. M122-1657		SERIAL NO. 06065-320		
LIST OF ART CITED BY APPLICANT Use several sheets if necessary.				APPLICANT Cem. Basceri et al.				
FILING DATE July 13, 2001				GROUP 1-3, 4, 6, 7				
U.S. PATENT DOCUMENTS								
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E	AA	5,256,453	10/26/93	Numasawa				
E	AB	5,731,048	01/21/97	Endo				
E	AC	5,776,254	03/24/98	Yializis et al.				
E	AD	5,783,253	07/07/98	Yuuki et al.				
E	AE	5,798,903	07/21/98	Roh				
E	AF	6,043,526	08/25/98	Diotre et al.				
E	AG	6,046,340	03/28/00	Ochian				
E	AH	6,078,492	04/04/00	Kadokura et al.				
E	AI	6,153,895	06/20/00	Huang et al.				
E	AJ	6,037,205	11/28/00	Watanabe				
E	AK	6,037,205	03/14/00	Huh et al.				
FOREIGN PATENT DOCUMENTS								
		Document Number	Date	Country	Class	Subclass	Translation	
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E	AL	0,855,715 A2	26/01/98	EPO - Zhao et al., Applied Materials, Inc.				
E	AM	0,957,522 A2	12/05/99	EPO - Ueda, Michihiro, Matsushita Electric Ind. Co.,				
E	AN	WO 98/9497	20/02/98	WIPO - Simpson, John et al.				
E	AO	0,474,140 A1	30/08/91	EPO - Kaniyama, Satoshi c/o NEC Corporation				
E	AP	WO 99/64645	11/06/99	WIPO - Narwankar et al., Applied Materials, Inc.				
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)								
E	AR		Steve Bilodeau et al., <i>Composition Dependence of the Dielectric Properties of MOCVD Ba/Sr TiO₂</i> , pp. 1-21 (MES Fall Meeting 12/01/94)					
E	AS		Steve M. Bilodeau et al., <i>MOCVD BST for High Density DRAM Applications</i> (Preprint for SEMICON/WEST 07/12/95), 2 page.					
E	AT		Y C Cheu et al., Abstract, <i>Improvements of the Properties of Chemical Vapor-Deposited (Ba,Sr)TiO₂ Films Through Use of a Seed Layer</i> , 16 JPN. J. APPL. PHYS. Pt. 1, No. 11, pp. 6824-6828 (1997)					
EXAMINER				DATE CONSIDERED				
								
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Filing Date AUG 29 2001				APPLICANT Cem. Bascom et al.				
				FILING DATE July 13, 2001		GROUP E-6		
U.S. PATENT DOCUMENTS								
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EF	AA	5,470,398	11/28/95	Shibuya et al.				
EF	AI	5,254,805	10/19/93	Kanayama				
EF	AG	6,156,638	12/05/00	Agarwal et al.				
EF	AI	6,165,834	12/26/00	Agarwal et al.				
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)								
EF	AF		Chung Ming Chu et al., Abstract, <i>Electrical properties and crystal structure of (Ba,Sr)TiO₃ films prepared at low temperatures</i>					
			on a LaSiO ₃ electrode by radio-frequency magnetron sputtering, 70 APPLIED PHYSICS LETTERS No. 2, pp. 249-251 (1997).					
EF	AG		Kazuhito Eguchi et al., Abstract, <i>Chemical vapor deposition of (Ba,Sr)TiO₃ thin films for application in gigabit scale</i>					
			dynamic random access memories, 14 INTEGRATED FERROELECTRICS Nos. 1-4, Pt. 1, pp. 33-42 (1997).					
EF	AF		Q.X. Jia et al., Abstract, <i>Structural and dielectric properties of Ba_{0.8}Sr_{0.2} thin films with an epi RuO₂ bottom electrode,</i>					
			19 INTEGRATED FERROELECTRICS Nos. 1-4, pp. 111-119 (1998).					
EXAMINER				DATE CONSIDERED				
				12/05/01				
*EXAMINER Initial if reference considered; whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.								

Form 10-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. MI22-1657	SERIAL NO. 09 965 320
LIST OF ART CITED BY APPLICANT Use several sheets if necessary.		APPLICANT Cem Basceri et al.	
FILING DATE July 13, 2001		GROUP Unknown	

U.S. PATENT DOCUMENTS							
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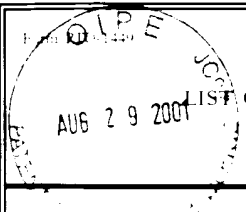

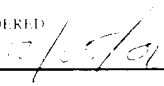
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	AO							
	AP							

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)			
EF	AR		Takaaki Kawahara et al., <i>(Ba, Sr)TiO₃ Films Prepared by Liquid Source Chemical Vapor Deposition on Ru Electrodes</i> , 35 JPN. J.
			APPL. PHYS. Pt. 1, No. 9B, pp. 4880, 4883 (1996).
EF	AS		Rajesh Khamankar et al., <i>A Novel Low-Temperature Process for High Dielectric Constant BST Thin Films for ULSI DRAM Applications</i> , Microelectronics Research Center, Univ. of Texas at Austin, TX (Undated), 2 pages
EF	AT		Yong Tae Kim et al., <i>Abstract, Advantages of RuO₄ bottom electrode in the dielectric and leakage characteristics of (Ba,Sr)TiO₃ capacitor</i> , 35 JPN. J. APPL. PHYS. Pt. 1, No. 12A, pp. 6153-6156 (1996).

EXAMINER 	DATE CONSIDERED 12/05/01
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Form PTO-147		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. M1221657		SERIAL NO. 09 905 320	
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				FILING DATE July 13, 2001		GROUP Unknown	
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)							
EF	AR		SH. Paek et al., Abstract, <i>Characterization of MIS capacitor of BST thin films deposited on Si by RF magnetron sputtering.</i>				
			Ferroelectric Thin Films V Symposium, San Francisco, CA, pp. 33-38 (April 7, 1995)				
EF	AS		N. Takeuchi et al., Abstract, <i>Effect of firing atmosphere on the cubic-hexagonal transition in Ba_{0.8} Sr_{0.2} TiO₃</i> , 98 JPN J. APPL. PHYS.				
			KERAMIKUSI KYOKAI GAKUJISU RONBUNSHI No. 8, pp. 836-839 (1990)				
EF	AT		H. Yamaguchi, et al., Abstract, <i>Reactive coevaporation synthesis and characterization of SrTiO₃, BaTiO₃ thin films</i> , IEEE				
			International Symposium on Applications of Ferroelectrics, Greenville, SC, pp. 285-288 (August 2, 1992)				
EXAMINER			DATE CONSIDERED				
<small>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</small>							

		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. MI22 1677		SERIAL NO. 09 005 320		
		LIST OF ART CITED BY APPLICANT <small>Use several sheets if necessary</small>						
		APPLICANT Carn. Bascari et al.				FILING DATE July 13, 2001		GROUP Unknown
U.S. PATENT DOCUMENTS								
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	AN							
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	AP							
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)								
EF	AR		S. Yamamichi et al., Abstract, <i>Ba + Sr/Ti ratio dependence of the dielectric properties for (Ba_{1-x}Sr_xTiO₃) thin films prepared by ion beam sputtering</i> , 64 APPLIED PHYSICS LETTERS No. 13, pp. 1644-1646 (1994).					
			M. Yamamuka et al., Abstract, <i>Thermal-Desorption Spectroscopy of (Ba,Sr,TiO₃) Thin-Films Prepared by Chemical-Vapor-Deposition</i> , 35 JPN J. OF APPL. PHYS. Pt. 1, No. 2A, pp. 729-735 (1996).					
EF	AS		Arai I., et al., <i>Preparation of SrTiO₃ Films on 8-Inch Wafers by Chemical Vapor Deposition</i> , Jap. Journal of Applied Physics, Vol. 35, No. 9B, Part 01, 09 01 96, Pgs. 4875-4879.					
EXAMINER				DATE CONSIDERED				
								
<small>*EXAMINER - Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</small>								

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CF	AR		Kim, et al. <i>Structural and Electrical Properties of BaTiO₃ grown on p-InP (100) by low-pressure metalorganic chemical vapor deposition at low temperature</i> , Applied Physics Letters, U.S. American Institute of Physics Vol. 65, No. 15, 10/10/94, Pgs. 1955-1957				
	AS						
	AI						
EXAMINER			DATE CONSIDERED				
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